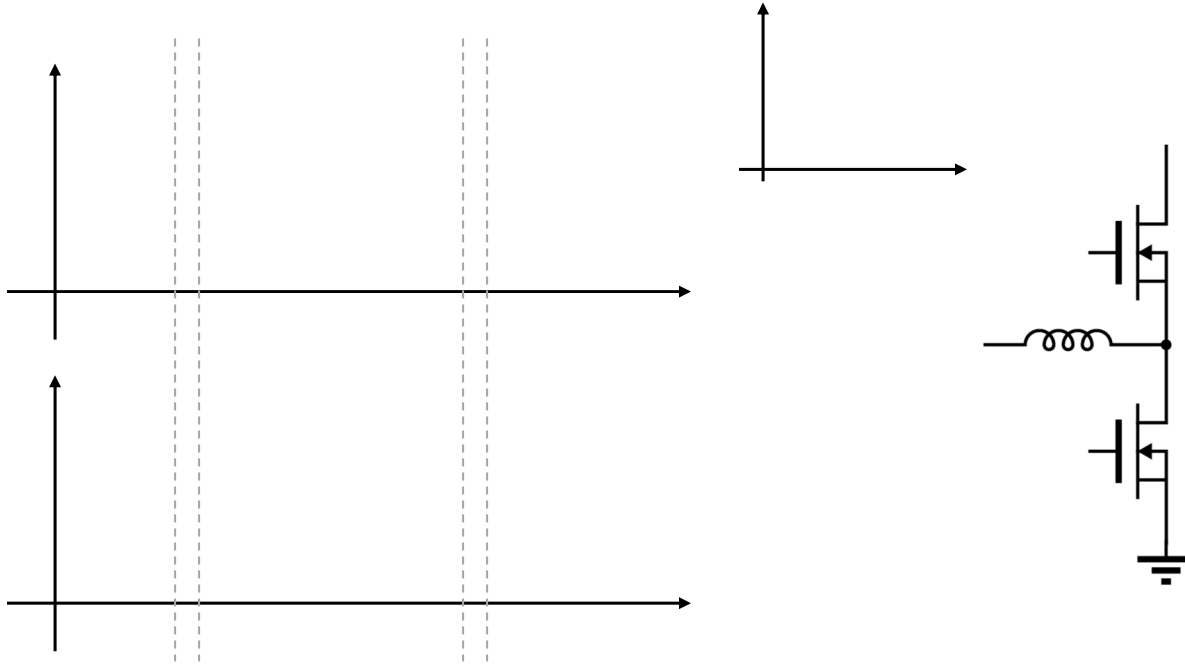
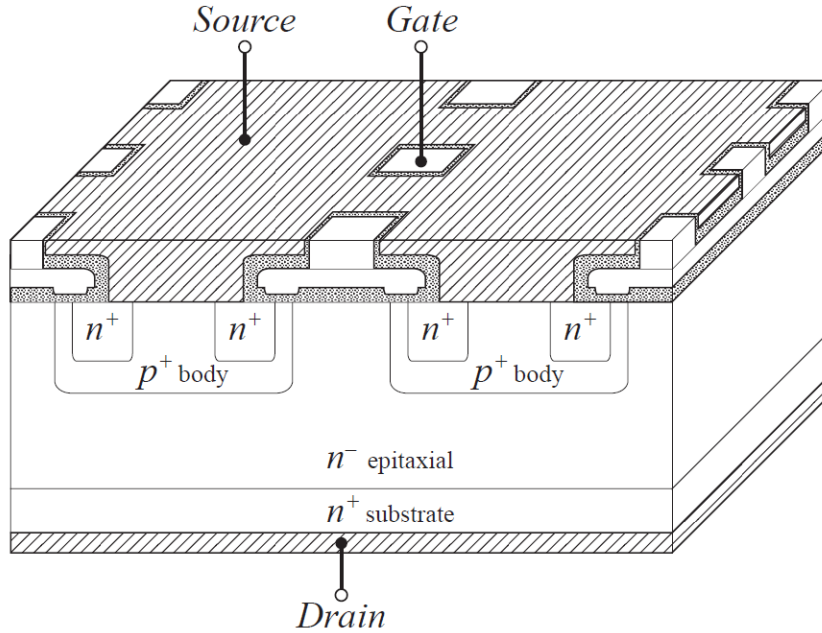


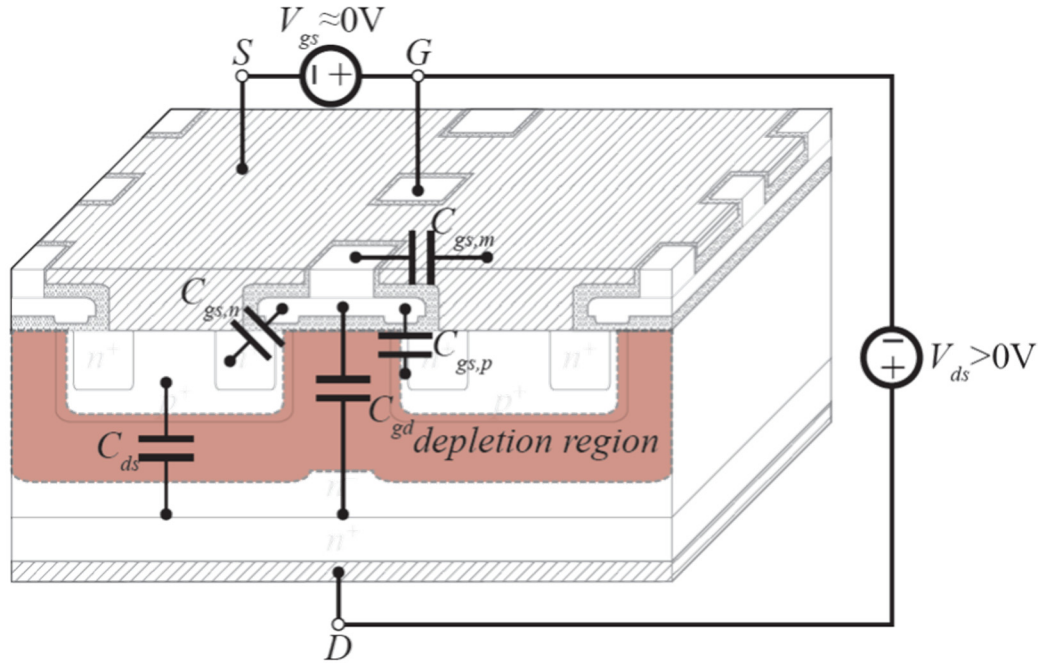
Synchronous Switching



MOSFET Cross Section



MOSFET Depletion Capacitance

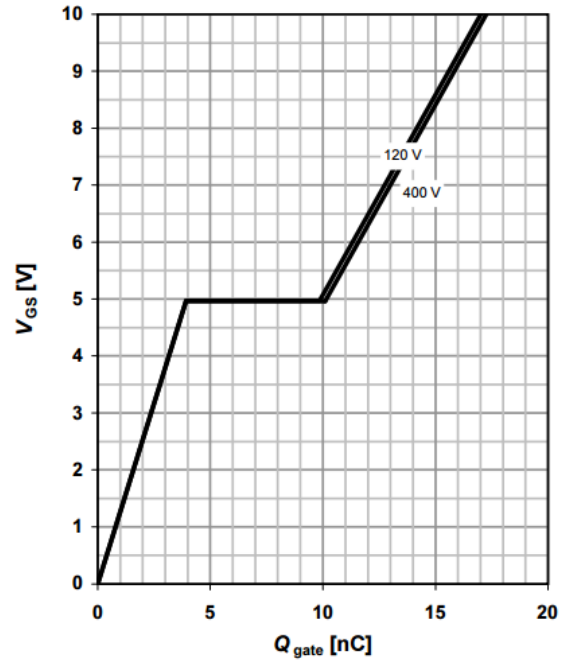


Gate Charge

9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=5.2$ A pulsed

parameter: V_{DD}



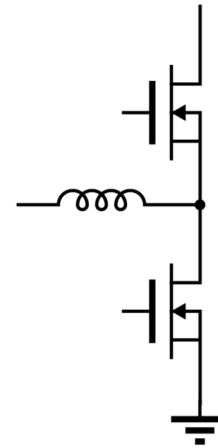
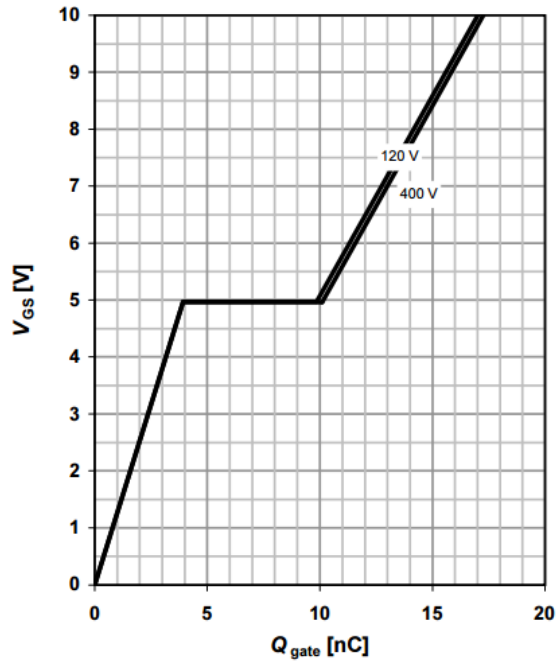
Overlap Time

9 Typ. gate charge

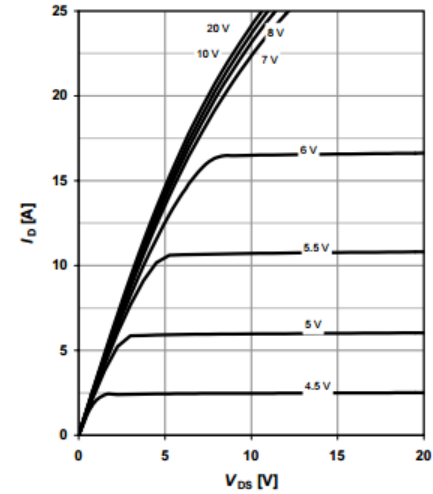
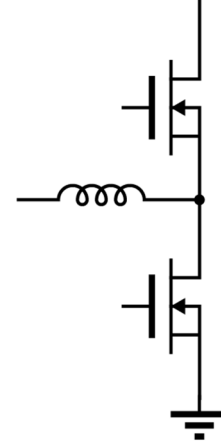
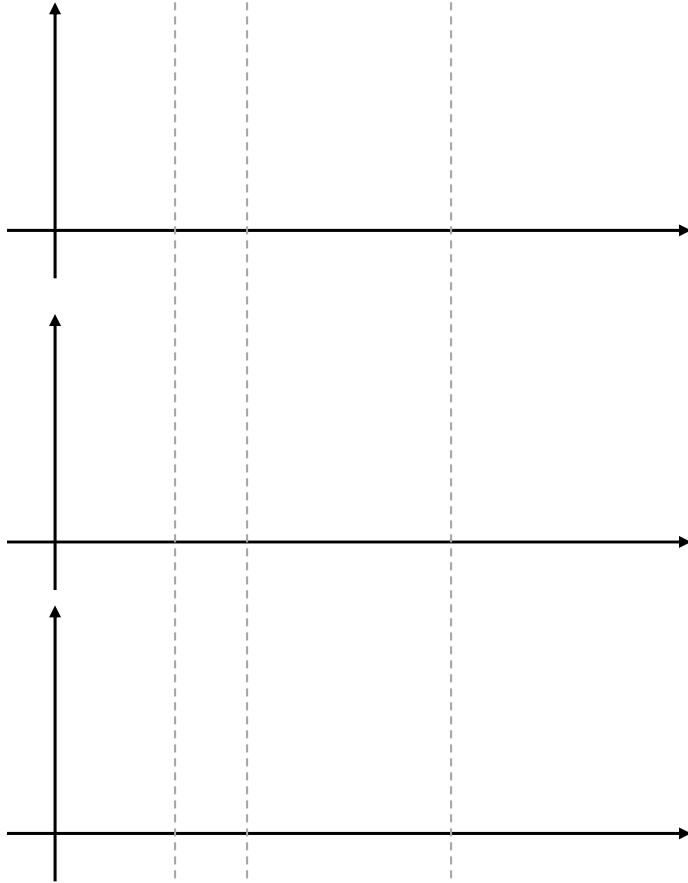
$V_{GS}=f(Q_{gate})$; $I_D=5.2$ A pulsed

parameter: V_{DD}

Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=0.34$ mA	2.5	3	3.5	
Gate resistance	R_G	$f=1$ MHz, open drain	-	1.8	-	Ω



FET Turn-On



Device Transconductance

